2SD2216G

Silicon NPN epitaxial planar type

For general amplification Complementary to 2SB1462G

■ Features

- \bullet High forward current transfer ratio h_{FE}
- ullet Low collector-emitter saturation voltage $V_{\text{CE(sat)}}$
- SS-Mini type package, allowing downsizing of the equipment and automatic insertion through the tape packing.

■ Absolute Maximum Ratings $T_a = 25$ °C

Parameter	Symbol	Rating	Unit	
Collector-base voltage (Emitter open)	V _{CBO}	60	V	
Collector-emitter voltage (Base open)	V _{CEO}	50	V	
Emitter-base voltage (Collector open)	V_{EBO}	7	V	
Collector current	I_C	100	mA	
Peak collector current	I _{CP}	200	mA	
Collector power dissipation	P _C	125	mW	
Junction temperature	T_{j}	125	°C	
Storage temperature	T _{stg}	-55 to +125	°C	

■ Package

- Code SSMini3-F3
- Marking Symbol: Y
- Pin Name
 - 1: Base
- 2: Emitter
- 3: Collector

■ Electrical Characteristics $T_a = 25$ °C ± 3 °C

Parameter	Symbol	Conditions	Min	Тур	Max	Unit
Collector-base voltage (Emitter open)	V _{CBO}	$I_{\rm C} = 10 \; \mu \text{A}, I_{\rm E} = 0$	60			V
Collector-emitter voltage (Base open)	V _{CEO}	$I_C = 2 \text{ mA}, I_B = 0$	50			V
Emitter-base voltage (Collector open)	V_{EBO}	$I_E = 10 \mu\text{A}, I_C = 0$	7			V
Collector-base cutoff current (Emitter open)	I _{CBO}	$V_{CB} = 20 \text{ V}, I_{E} = 0$			0.1	μΑ
Collector-emitter cutoff current (Base open)	I _{CEO}	$V_{CE} = 10 \text{ V}, I_{B} = 0$			100	μΑ
Forward current transfer ratio	h _{FE1} *2	$V_{CE} = 10 \text{ V}, I_{C} = 2 \text{ mA}$	160		460	_
	h _{FE2} *1	$V_{CE} = 2 \text{ V}, I_{C} = 100 \text{ mA}$	90			
Collector-emitter saturation voltage	V _{CE(sat)}	$I_C = 100 \text{ mA}, I_B = 10 \text{ mA}$		0.1	0.3	V
Transition frequency	f_T	$V_{CB} = 10 \text{ V}, I_E = -2 \text{ mA}, f = 200 \text{ MHz}$		150		MHz
Collector output capacitance	C _{ob}	$V_{CB} = 10 \text{ V}, I_E = 0, f = 1 \text{ MHz}$		3.5		pF
(Common base, input open circuited)						

Note) 1. Measuring methods are based on JAPANESE INDUSTRIAL STANDARD JIS C 7030 measuring methods for transistors.

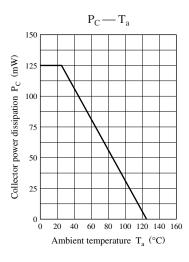
2. *1: Pulse measurement

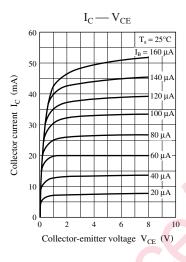
*2: Rank classification

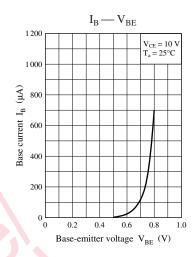
Rank	Q	R	S	No rank
h _{FE1}	160 to 260	210 to 340	290 to 460	180 to 390

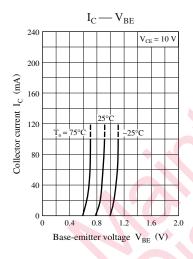
Product of no-rank is not classified and have no marking symbol for rank.

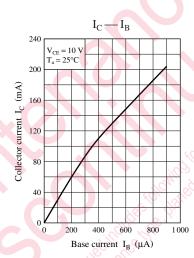
Panasonic

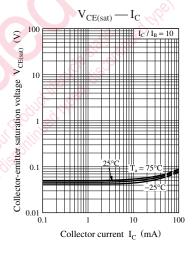


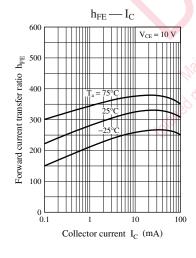


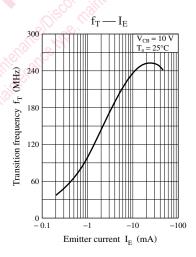












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